TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

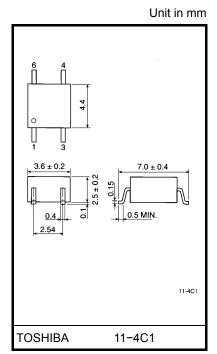
# **TLP126**

# Programmable Controllers AC / DC-Input Module Telecommunication

The TOSHIBA mini flat coupler TLP126 is a small outline coupler, suitable for surface mount assembly.

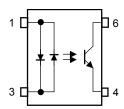
TLP126 consists of a photo transistor, optically coupled to a gallium arsenide infrared emitting diode connected inverse parallel, and provides high CTR at low AC input current.

- Collector-emitter voltage: 80 V (min.)
- Current transfer ratio: 100% (min.)
- Isolation voltage: 3750Vrms (min.)
- UL recognized: UL1577, file No. E67349



Weight: 0.09 g

# Pin Configurations (top view)



- 1: Anode, Cathode
- 3 : Cathode, Anode
- 4 : Emitter
- 6: Collector

#### Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
	Forward current	I <sub>F(RMS)</sub>	50	mA
ED	Forward current derating (Ta≥ 53°C) Δ	ΔI <sub>F</sub> / °C	-0.7	mA / °C
۳	Peak forward current(100µs pulse,100pps)	IFP	1	Α
	Junction temperature	Tj	125	°C
	Collector-emitter voltage	V <sub>CEO</sub>	80	٧
	Emitter-collector voltage	V <sub>ECO</sub>	7	٧
o	Collector current	IC	50	mA
Detector	Peak collector current(10ms pulse,100pps)	I <sub>CP</sub>	100	mA
ă	Power dissipation	PC	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP <sub>C</sub> / °C	-1.5	mW / °C
	Junction temperature	Tj	125	°C
Stor	rage temperature range	T <sub>stg</sub>	-55~125	°C
Оре	erating temperature range	T <sub>opr</sub>	-55~100	°C
Lea	d soldering temperature(10 sec.)	T <sub>sold</sub>	260	°C
Tota	al package power dissipation	PT	200	mW
Tota	al package power dissipation derating (Ta≥25°C)	ΔP <sub>T</sub> / °C	ΔP <sub>T</sub> / °C –2.0	
Isola	ation voltage (AC, 1min., RH ≤ 60%) (Note 1)	BVS	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: Pins1, and 3 shorted together and 4 and 6 shorted together.

#### **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>CC</sub>	_	5	48	V
Forward current	I <sub>F(RMS)</sub>	_	1.6	20	mA
Collector current	IC	_	1	10	mA
Operating temperature	T <sub>opr</sub>	-25	_	75	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

### Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	$V_{F}$	I <sub>F</sub> = ±10 mA	1.0	1.15	1.3	V
F	Capacitance	C <sub>T</sub>	V = 0, f = 1 MHz		60		pF
	Collector–emitter breakdown voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> = 0.5 mA	80			٧
Detector	Emitter-collector breakdown voltage	V <sub>(BR)</sub> ECO	I <sub>E</sub> = 0.1 mA	7	_		٧
Dete	Collector dark current	lana	V <sub>CE</sub> = 48 V		10	100	nA
	Collector dark current	ICEO	V <sub>CE</sub> = 48 V, Ta = 85°C		2	50	μΑ
	Capacitance collector to emitter	C <sub>CE</sub>	V = 0, f = 1 MHz		12	_	pF

#### **Coupled Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	Mln.	Тур.	Max.	Unit
Current transfer ratio	I <sub>C</sub> / I <sub>F</sub>	$I_F = \pm 1$ mA, $V_{CE} = 0.5$ V	100	_	1200	%
Low input CTR	I <sub>C</sub> / I <sub>F (low)</sub>	IF = ±0.5 mA, V <sub>CE</sub> = 1.5 V	50	_	_	%
Collector-emitter	Vo= ( 1)	I <sub>C</sub> = 0.5 mA, I <sub>F</sub> = ±1 mA	_	_	0.4	V
saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = 1 mA, I <sub>F</sub> = ±1 mA	_	0.2	_	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Off-state collector current	I <sub>C(off)</sub>	V <sub>F</sub> = ± 0.7V, V <sub>CE</sub> = 48 V	_	1	10	μΑ
CTR symmetry	I <sub>C (ratio)</sub>	$I_{C} (I_{F} = -1mA) / I_{C} (I_{F} = 1mA)$	0.3	_	3	_

### Coupled Electrical Characteristics (Ta = $-25\sim75^{\circ}$ C)

Characteristic	Symbol	Test Condition	MIn.	Тур.	Max.	Unit
Current transfer ratio	I <sub>C</sub> / I <sub>F</sub>	I <sub>F</sub> = 1 mA, V <sub>CE</sub> = 0.5 V	50	_	_	%
Low input CTR	I <sub>C</sub> / I <sub>F (low)</sub>	IF = 0.5 mA, V <sub>CE</sub> = 1.5 V	_	50	_	%

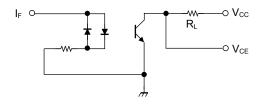
## Isolation characteristics (Ta = 25°C)

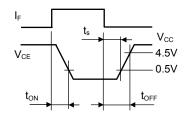
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V <sub>S</sub> = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
	-	AC, 1 minute	3750	_	_	- Vrms
Isolation voltage		AC, 1 second, in oil	_	10000	_	
		DC, 1 minute, in oil	_	10000	_	Vdc

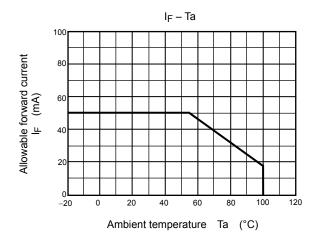
## **Switching Characteristics (Ta = 25°C)**

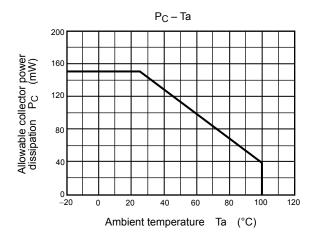
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	t <sub>r</sub>		_	8	_	
Fall time	t <sub>f</sub>	$V_{CC} = 10 \text{ V}, I_{C} = 2 \text{ mA}$ $R_{L} = 100\Omega$	_	8	_	μs
Turn-on time	t <sub>on</sub>		_	10	_	μδ
Turn-off time	t <sub>off</sub>		_	8	_	
Turn-on time	t <sub>ON</sub>		_	10	_	
Storage time	t <sub>S</sub>	$R_L = 4.7 \text{ k}\Omega$ (Fig.1) $V_{CC} = 5 \text{ V}, I_F = \pm 1.6 \text{ mA}$	_	50	_	μs
Turn-off time	toff		_	300	_	

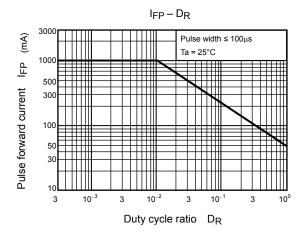
Fig. 1 Switching time test circuit

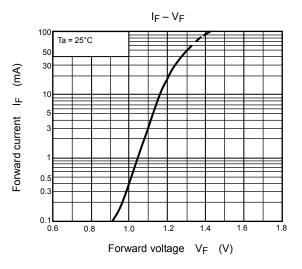


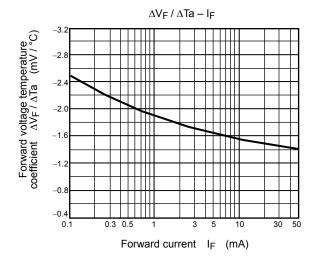


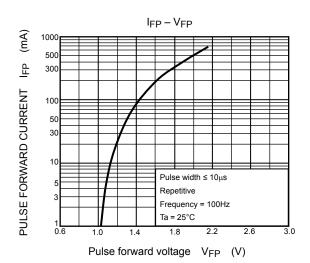


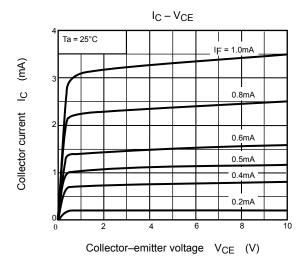


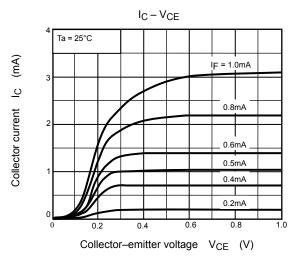


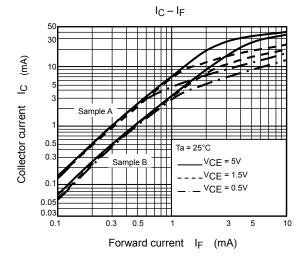


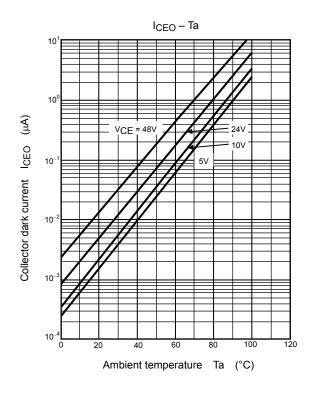


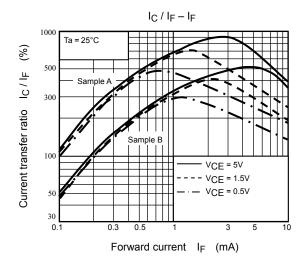




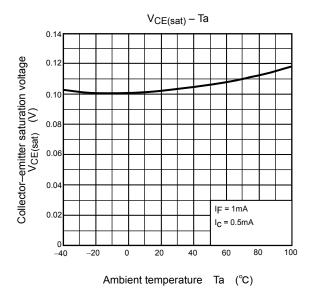


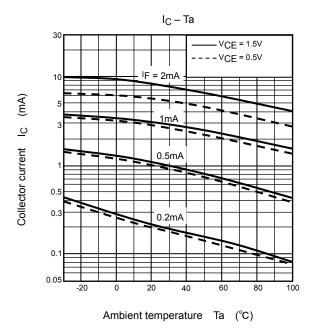


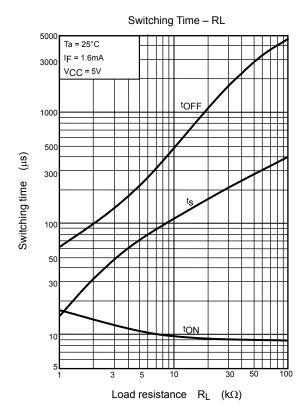




6 2007-10-01







2007-10-01

7

#### **RESTRICTIONS ON PRODUCT USE**

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
  may result from its use. No license is granted by implication or otherwise under any patents or other rights of
  TOSHIBA or the third parties.
- GaAs(Gallium Arsenide) is used in this product. The dust or vapor is harmful to the human body. Do not break, cut, crush or dissolve chemically.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
  compatibility. Please use these products in this document in compliance with all applicable laws and regulations
  that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
  occurring as a result of noncompliance with applicable laws and regulations.

8